

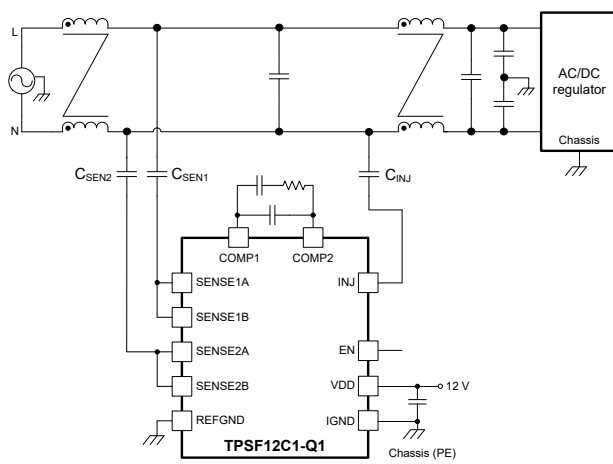
TPSF12C1-Q1 Standalone Active EMI Filter for Common-mode Noise Mitigation in Single-Phase AC Automotive Power Systems

1 Features

- AEC-Q100 qualified for automotive applications:
 - Device temperature grade 1: -40°C to $+125^{\circ}\text{C}$ ambient operating temperature
- **Functional Safety-Capable**
 - [Documentation available to aid functional safety system design](#)
- Voltage-sense, current-inject active EMI filter
 - Optimized for CISPR 25 Class 5 automotive EMI requirements
 - Low impedance for common-mode emissions
 - 50%+ reduction in choke size, weight and cost
 - Peak inject current of ± 80 mA (typical)
- Wide supply voltage range of 8 V to 16 V
- -40°C to 150°C junction temperature range
- Simple configuration for single-phase AC systems
 - Integrated sensing filter and summing network
 - Low leakage current at line frequency
 - Simplified compensation network
- Inherent protection features for robust design
 - Withstands 5-kV surge (IEC 61000-4-5) with minimal external component count
 - Enable pin for remote ON and OFF control
 - VDD voltage UVLO protection with hysteresis
 - Thermal shutdown protection with hysteresis
- 4.2-mm \times 2-mm SOT-23 14-pin (DYY) package

2 Applications

- [On-board charger and isolated DC/DC](#) for EVs
- [Isolated DC/DC for servers, AC/DC for telecom](#)
- [Inverters](#) and [HVAC motor control](#)



Simplified Schematic

3 Description

The TPSF12C1-Q1 is an active filter IC designed to reduce common-mode (CM) electromagnetic interference (EMI) in single-phase AC power systems.

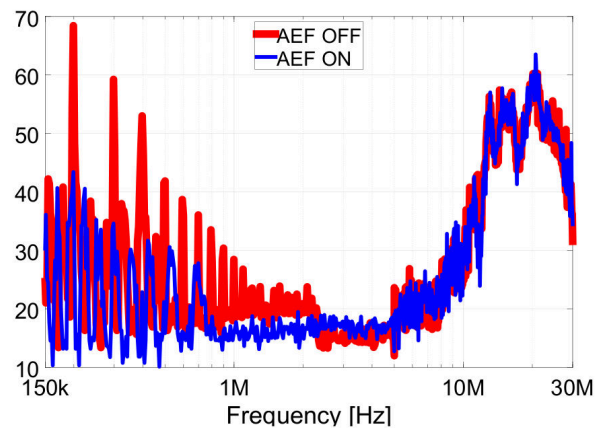
The active EMI filter (AEF) configured with voltage sense and current inject (VSCI) uses a capacitive multiplier circuit to emulate the Y-capacitors in a conventional passive filter design. The device senses the high-frequency noise on each power line using a set of sense capacitors and injects noise-canceling currents back into the power lines using an injection capacitor. The effective active capacitance is set by the circuit gain and the injection capacitance. The AEF sensing and injection impedances use relatively low capacitance values with small component footprints. The device includes integrated filtering, compensation and protection circuitry, and an enable input.

The TPSF12C1-Q1 provides a very low impedance path for CM noise in the frequency range of interest for EMI measurement. Enabling up to 25 dB of CM noise reduction at the lower end of specified frequency ranges (for example, 150 kHz to 3 MHz) significantly reduces the size, weight and cost of the CM filter implementation.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
TPSF12C1-Q1	DYY (SOT-23-THIN, 14)	4.20 mm \times 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.



EMI Mitigation Result



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4 Revision History

DATE	REVISION	NOTES
November 2022	*	Advance Information initial release

5 Device Comparison Table

DEVICE	ORDERABLE PART NUMBER	PHASES	GRADE	JUNCTION TEMPERATURE RANGE
TPSF12C1-Q1	TPSF12C1QDYRQ1	1	Automotive	-40°C to 150°C
TPSF12C3-Q1	TPSF12C3QDYRQ1	3	Automotive	-40°C to 150°C
TPSF12C1	TPSF12C1DYR	1	Commercial	-40°C to 150°C
TPSF12C3	TPSF12C3DYR	3	Commercial	-40°C to 150°C

6 Pin Configuration and Functions

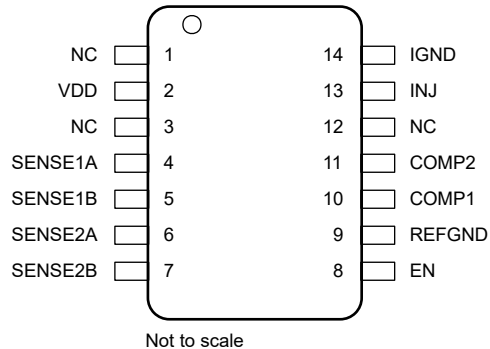


Figure 6-1. 14-Pin SOT-23-THIN DYY Package (Top View)

Table 6-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NO.	NAME		
1, 3, 12	NC	–	No internal connection. Tie to the GND plane on the PCB.
2	VDD	P	Power supply for IC. Bypass to IGND with a 1-μF X7R ceramic capacitor.
4	SENSE1A	I	Sense input (power line or neutral)
5	SENSE1B	I	Sense input (power line or neutral)
6	SENSE2A	I	Sense input (power line or neutral)
7	SENSE2B	I	Sense input (power line or neutral)
8	EN	I	Enable signal to activate noise cancellation
9	REFGND	G	Reference ground (Kelvin connected to IGND)
10	COMP1	I	Connection 1 for external compensation circuit
11	COMP2	I	Connection 2 for external compensation circuit
13	INJ	O	Injection signal output
14	IGND	G	Injection ground

(1) P = Power, G = Ground, I = Input, O = Output

7 Specifications

7.1 Absolute Maximum Ratings

Over the recommended operating junction temperature range of -40°C to 150°C (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
Pin voltage	VDD to IGND and REFGND	-0.3	18	V
Pin voltage	SENSE1A, SENSE1B, SENSE2A, SENSE2B to REFGND	-5.5	5.5	V
Pin voltage	COMP1 to IGND and REFGND	-0.3	5.5	V
Pin voltage	COMP2 to IGND and REFGND	-0.3	15	V
Pin voltage	INJ to IGND	-0.3	$V_{\text{VDD}} + 0.3$	V
Pin voltage	EN to IGND and REFGND	-0.3	18	V
Pin voltage	IGND to REFGND	-0.3	0.3	V
Sink current	INJ		150	mA
Source current	INJ		150	mA
T_{J}	Operating junction temperature	-40	150	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-55	150	$^{\circ}\text{C}$

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

7.2 ESD Ratings

			VALUE	UNIT	
$V_{\text{(ESD)}}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾ HBM ESD classification level 2	± 2000	V	
		Charged device model (CDM), per AEC Q100-011 CDM ESD classification level C4B	Corner pins (1, 7, 8, and 14)		± 750
			Other pins		± 500

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

Over the recommended operating junction temperature range of -40°C to 150°C (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{VDD}	VDD voltage range	8	12	16	V
V_{INJ}	Output voltage range	2		$V_{\text{VDD}} - 2$	V
V_{SENSE}	Sense voltage range	-5		5	V
V_{EN}	Pin voltage	0		16	V
I_{INJ}	Output current range			80	mA
			Source and sink magnitude		
T_{A}	Operating ambient temperature	-40		105	$^{\circ}\text{C}$

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DYY (SOT-23-THIN)	UNIT
		14 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	110	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	54	°C/W
R _{θJB}	Junction-to-board thermal resistance	35	°C/W
ψ _{JT}	Junction-to-top characterization parameter	2.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	35	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

7.5 Electrical Characteristics

Limits apply over the junction temperature (T_J) range of –40°C to 150°C, unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at T_J = 25°C, and are provided for reference purposes only. Unless otherwise stated, the following conditions apply: V_{VDD} = 12 V⁽¹⁾.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY						
I _Q	VDD quiescent current	SENSE1A, SENSE1B, SENSE2A, and SENSE2B grounded, V _{EN} = 5 V, 8 V < V _{VDD} < 16 V	6.25	12.5	23.5	mA
I _{SD}	VDD shutdown supply current	V _{EN} = 0 V		50		µA
SUPPLY VOLTAGE UVLO						
VDD _{UVLO(R)}	UVLO rising threshold	V _{VDD} rising	7.5	7.7	7.95	V
VDD _{UVLO(F)}	UVLO falling threshold	V _{VDD} falling	6.4	6.7	7.0	V
VDD _{UVLO(H)}	UVLO hysteresis			0.96		V
ENABLE						
V _{EN_H}	EN voltage high		2.2			V
V _{EN_L}	EN voltage low				0.8	V
R _{EN}	EN pin pull-up resistance to VDD	V _{EN} = 0 V		900		kΩ
I _{EN(LKG)}	EN input leakage current	V _{EN} = 12 V		850		nA
INPUT FILTER NETWORK						
A _{CM}	Gain from shorted power lines through single sense cap, C _{SEN} , to COMP1 pin vs. REFGND	C _{SEN} = 2 µF, 60 Hz		–42		dB
		C _{SEN} = 2 µF, 50 kHz		–4		
		C _{SEN} = 2 µF, 500 kHz ⁽²⁾		–1.5		
		C _{SEN} = 2 µF, 1 MHz ⁽²⁾		–1		
A _{DM}	Gain from differential signal applied to SENSE lines to COMP1 pin vs. REFGND	SENSE1A shorted to SENSE1B, SENSE2A shorted to SENSE2B, C _{SEN1} = C _{SEN2} = 1 µF, 60 Hz		–78		dB
		SENSE1A shorted to SENSE1B, SENSE2A shorted to SENSE2B, C _{SEN1} = C _{SEN2} = 1 µF, 1 kHz		–59		
		SENSE1A shorted to SENSE1B, SENSE2A shorted to SENSE2B, C _{SEN1} = C _{SEN2} = 1 µF, 500 kHz ⁽²⁾		–35		
		SENSE1A shorted to SENSE1B, SENSE2A shorted to SENSE2B, C _{SEN1} = C _{SEN2} = 1 µF, 1 MHz ⁽²⁾		–36		
		SENSE1A shorted to SENSE1B, SENSE2A shorted to SENSE2B, C _{SEN1} = C _{SEN2} = 1 µF, 10 MHz ⁽²⁾		–35		

7.5 Electrical Characteristics (continued)

Limits apply over the junction temperature (T_J) range of -40°C to 150°C , unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at $T_J = 25^{\circ}\text{C}$, and are provided for reference purposes only. Unless otherwise stated, the following conditions apply: $V_{\text{VDD}} = 12\text{ V}$ ⁽¹⁾.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
AMPLIFIER						
A_{DC}	DC gain		53	58	62	dB
F_{BW}	Unity gain bandwidth			113		MHz
F_{BW}	40 dB bandwidth			1		MHz
V_{OFST}	COMP1 offset voltage			2		V
$V_{\text{INJ_MAX}}$	Maximum output voltage for linear operation	10% drop in gain	$V_{\text{VDD}} - 2$			V
$V_{\text{INJ_MIN}}$	Minimum output voltage for linear operation	10% drop in gain			2	V
$I_{\text{INJ_MAX_OP}}$	INJ current at linearity limits	$V_{\text{INJ}} = V_{\text{VDD}} - 2\text{ V}$	80			mA
		$V_{\text{INJ}} = V_{\text{IGND}} + 2\text{ V}$			-80	mA
PSRR						
PSRR_{10}		$8\text{ V} < V_{\text{VDD}} < 16\text{ V}$, See recommended feedback network, 10 kHz		0		dB
PSRR_{100}		$8\text{ V} < V_{\text{VDD}} < 16\text{ V}$, See recommended feedback network, 100 kHz		6		
STARTUP						
t_{W}	Startup delay	Period from $V_{\text{DD}} = \text{EN}$ applied until output valid		43		ms
t_{SU}	EN high to valid output			12		ms
t_{SD}	EN low to stop output signal			55		μs
THERMAL SHUTDOWN						
$T_{\text{J-SHD}}$	Thermal shutdown threshold ⁽²⁾	Temperature rising		175		$^{\circ}\text{C}$
$T_{\text{J-HYS}}$	Thermal shutdown hysteresis ⁽²⁾			20		$^{\circ}\text{C}$

- (1) MIN and MAX limits are 100% production tested at 25°C unless otherwise specified. Limits over the operating temperature range verified through correlation using Statistical Quality Control (SQC) methods. Limits are used to calculate Average Outgoing Quality Level (AOQL).
- (2) Parameter specified by design, statistical analysis and production testing of correlated parameters.

7.6 System Characteristics

The following specifications apply only to the typical applications circuit, with nominal component values. Specifications in the typical (TYP) column apply to $T_J = 25^{\circ}\text{C}$ and $V_{\text{VDD}} = 12\text{ V}$ only. Specifications in the minimum (MIN) and maximum (MAX) columns apply to the case of typical components over the temperature range of $T_J = -40^{\circ}\text{C}$ to 150°C . These specifications are not ensured by production testing.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY						
I_{SUPPLY}	Input supply current with INJ loaded			15		mA

8 Detailed Description

8.1 Overview

The TPSF12C1-Q1 is an active electromagnetic interference (EMI) filter controller that is designed to reduce common-mode (CM) conducted emissions in off-line power converter systems. The device senses the high-frequency noise on each power line using a set of Y-rated capacitors, C_{SEN1} and C_{SEN2} , then injects noise-canceling currents back into the power lines using a Y-rated capacitor C_{INJ} along with damping circuitry that ensures stability. The device includes integrated filtering, compensation and protection circuitry.

The TPSF12C1-Q1 provides a very low impedance path for CM noise in the frequency range of interest for EMI measurement. This feature can achieve approximately 15 to 25 dB of CM noise reduction over the frequency range of interest, for example, 150 kHz to 3 MHz, helping to reduce the size of common-mode chokes.

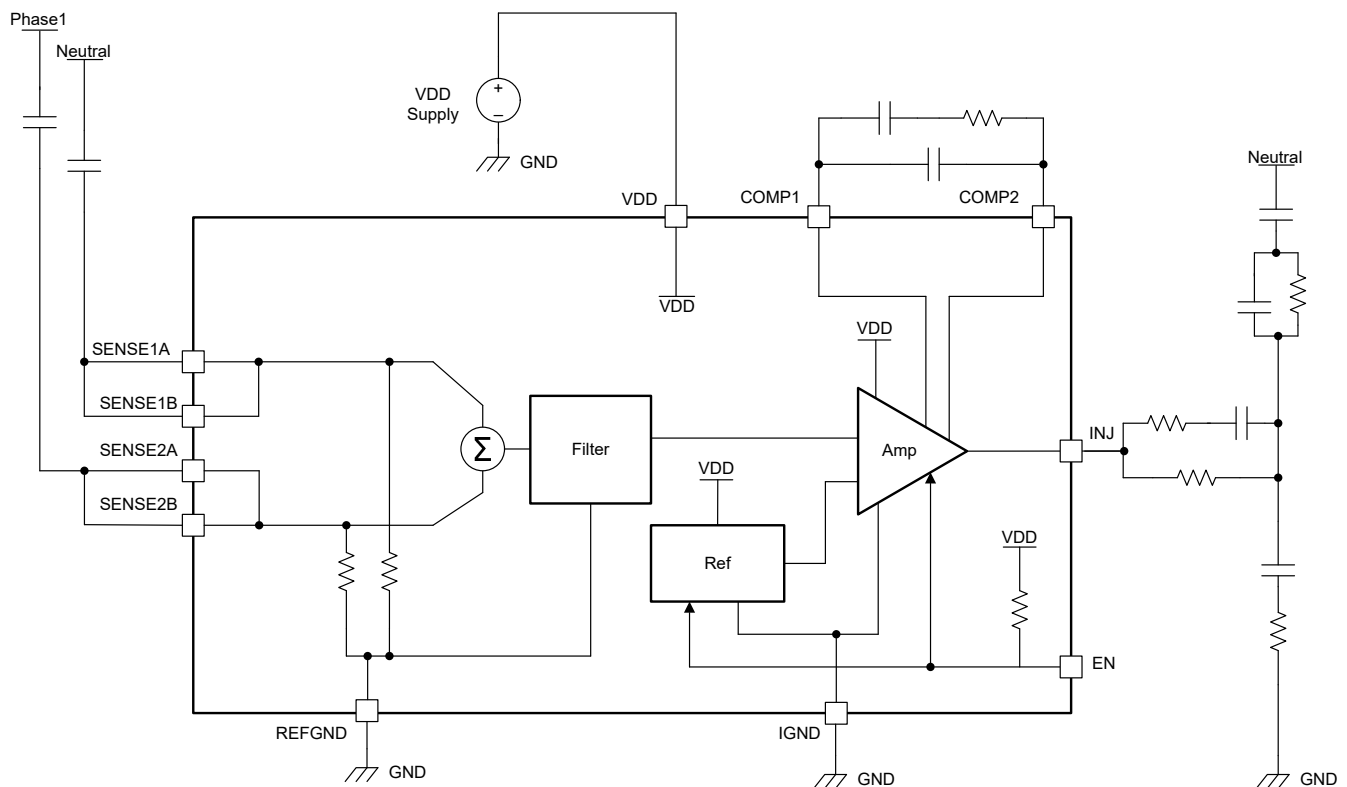
The TPSF12C1-Q1 operates over a supply voltage range of 8 V to 16 V and can withstand 18 V. The device features include:

- Internal circuitry that simplifies compensation and design
- Built-in supply voltage UVLO to ensure proper operation
- Built-in thermal shutdown protection
- An EN input that allows power saving when the system is idling

The active EMI feature significantly reduces EMI filtering cost, size, and weight, while helping to meet CISPR 25 Class 5 EMI limits for conducted and radiated emissions.

Leveraging a pin arrangement designed for simple layout that requires relatively few external components, the TPSF12C1-Q1 is specified for maximum ambient and junction temperatures of 105°C and 150°C, respectively.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Integrated Line Filter

The TPSF12C1-Q1 has a built-in input line filter. Because the entire filter is integrated in the device, matching is better than what can be achieved using discrete components. This filter not only removes virtually all input at line frequency, it also sums the signals from the sense inputs to create a signal that represents the common-mode noise signature without line-frequency components.

8.3.2 Compensation

The TPSF12C1-Q1 contains partial internal compensation that, when combined with two capacitors and a resistor between COMP1 and COMP2, forms a lead-lag network. This internal network allows fewer external components to be used.

8.3.3 Enable

The TPSF12C1-Q1 has an enable input, EN, that allows the device to be shut down, drastically reducing power consumption during intervals when EMI mitigation is not required. The typical quiescent current consumption is 12.5 mA and 50 μ A when the device is enabled and disabled, respectively. Because many designs do not use this feature, a 900-k Ω pull up resistor connects internally between VDD and EN, allowing the EN pin to be left open.

In addition, INJ is pulled low when the device is disabled to reduce the parasitic resistance in series with C_{INJ}.

8.3.4 Supply Voltage UVLO Protection

To ensure that the TPSF12C1-Q1 operates safely while VDD is powered on and off as well as during brownout conditions, this device has a built-in UVLO protection to provide predictable behavior while VDD is below its operating voltage. UVLO releases when the VDD voltage exceeds 7.95 V, allowing normal operation. UVLO engages if the VDD voltage falls below approximately 6.6 V. There is approximately 1 V of UVLO hysteresis.

8.3.5 Thermal Shutdown Protection

The TPSF12C1-Q1 provides built-in overtemperature protection that shuts down the device if the junction temperature exceeds approximately 175°C. After junction temperature drops by approximately 20°C, the device restarts. This process is repeated until the ambient temperature or power dissipation is reduced.

8.4 Device Functional Modes

8.4.1 Shutdown Mode

The EN pin provides ON and OFF control for the TPSF12C1-Q1. When the EN voltage is below approximately 0.8 V, the device is in shutdown mode. Most internal circuitry is shutdown. The quiescent current in shutdown mode drops to 50 μ A (typical). The TPSF12C1-Q1 also employs VDD internal undervoltage protection. If the VDD voltage is below its UV threshold, the IC remains off. The INJ output pulls to ground while in shutdown mode.

8.4.2 Active Mode

The TPSF12C1-Q1 is in active mode when V_{VDD} is above its UVLO threshold, EN is high, and there is no overtemperature fault. The simplest way to enable operation is to connect EN to VDD, which allows startup when the applied supply voltage exceeds the UVLO threshold voltage. In this mode, the device amplifies signals on COMP2 and outputs the amplified signal on the INJ pin.

9 Applications and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The TPSF12C1-Q1 common-mode AEF IC helps to improve the CM EMI signature of single-phase power systems. The device provides a very low impedance path for CM noise in the frequency range of interest for EMI measurement and helps to meet prescribed limits for EMI standards, such as:

- CISPR 11, EN 55011 – Industrial, Scientific and Medical (ISM) applications
- CISPR 25, EN 55025 – Automotive applications
- CISPR 32, EN 55032 – Multimedia applications

To expedite and streamline the process of designing of a TPSF12C1-Q1-based solution, a comprehensive TPSF12C1-Q1 [quickstart calculator](#) is available by download to assist the system designer with component selection for a given application.

9.2 Typical Applications

For the circuit schematic, bill of materials, PCB layout files, and test results of a TPSF12C1-Q1-powered implementation, see the TPSF12C1-Q1 [EVM](#).

9.2.1 Design 1 – AEF Circuit for High-Density On-Board Charger (OBC) in Electric Vehicles (EVs)

Figure 9-1 shows a schematic diagram of a 6.6-kW high-density OBC with conventional two-stage passive EMI filter. The CM chokes and Y-capacitors provide CM filtering, whereas the leakage inductance of the CM chokes and the X-capacitors provide DM filtering. Similar to TI reference design [TIDM-02013](#), the circuit uses a two-phase totem-pole (TTPL) power-factor correction (PFC) front-end followed by a full-bridge CLLC topology with active synchronous rectification.

The TTPL PFC stage runs at a fixed switching frequency of 120 kHz. The CLLC isolated DC/DC stage runs at a variable frequency from 200 kHz to 800 kHz (500-kHz nominal) and provides galvanic isolation in addition to battery voltage and current regulation. Even though the use of [LMG3522-Q1](#) GaN switches enables an open-frame power density of 3.8 kW/L, the conventional passive EMI filter occupies over 20% of the total solution size.

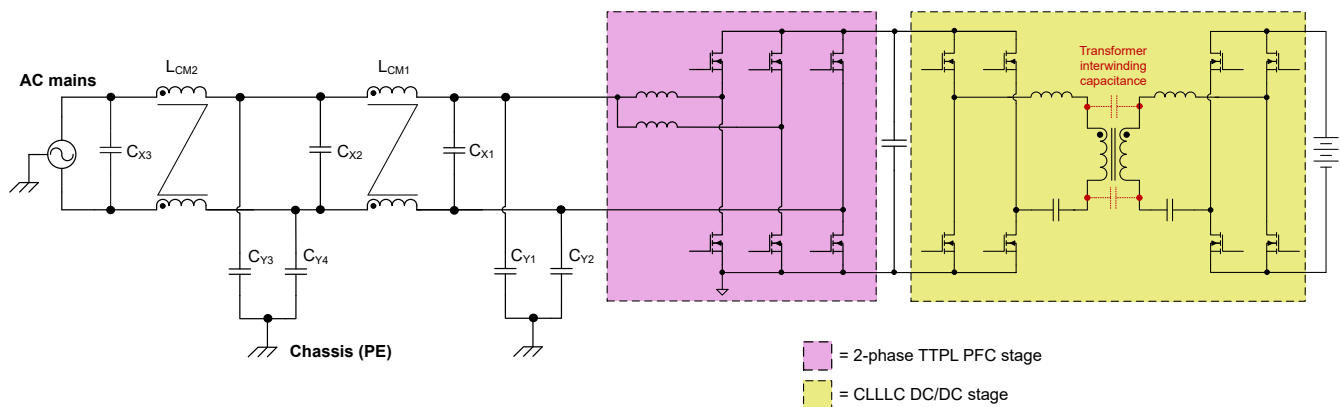


Figure 9-1. Circuit Schematic of an OBC With a Conventional Two-Stage EMI Filter

Note that the DC/DC stage in particular increases the CM EMI signature based on the high dv/dt of the GaN switches, the transformer interwinding capacitance as well as the various switch-node parasitic capacitances to chassis ground.

This application example replaces the two Y-capacitors, designated as C_{Y3} and C_{Y4} in Figure 9-1, with a single-phase AEF circuit using the TPSF12C1-Q1. See Figure 9-2. The AEF circuit provides capacitive multiplication, which reduces the inductance value and thus the size, weight, and cost of the CM chokes, now designated as $L_{CM1-AEF}$ and $L_{CM2-AEF}$. The total capacitance of the sense and inject capacitors is kept less than or equal to that of the replaced Y-capacitors, which results in the the total line-frequency leakage current remaining effectively unchanged or reduced.

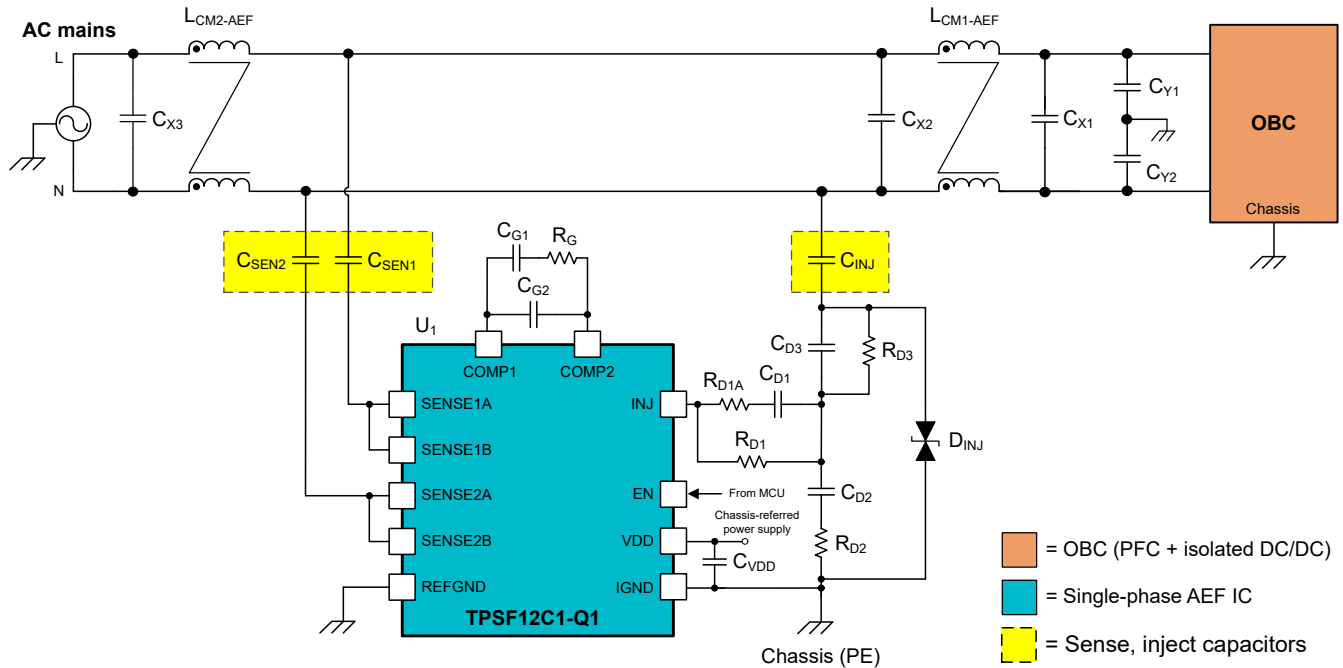


Figure 9-2. Circuit Schematic of an OBC With AEF Circuit Connected

9.2.1.1 Design Requirements

Table 9-1 shows the intended operating parameters for this application example.

Table 9-1. Design Parameters

DESIGN PARAMETER	VALUE
AC input voltage range	85 V to 265 V RMS
AC input line frequency	47 Hz to 63 Hz
Input RMS current (maximum)	32 A
DC output voltage range	250 V to 450 V
Rated output power	6.6 kW
Output current (maximum)	20 A
AC/DC stage switching frequency (fixed)	120 kHz
DC/DC stage switching frequency (variable)	200 kHz to 800 kHz

9.2.1.2 Detailed Design Procedure

Table 9-2 gives the selected component values, which are the same as those used in the TPSF12C1-Q1 EVM. This design uses a TVS diode placed at the low-voltage side of the inject capacitor for clamping during input surge conditions.

Table 9-2. AEF Circuit Components for Application Circuit 1

REFERENCE DESIGNATOR	QTY	SPECIFICATION	MANUFACTURER ⁽¹⁾	PART NUMBER
C _{SEN1} , C _{SEN2}	2	Capacitor, ceramic, 680 pF, 300 VAC, Y2	MuRata	DE2B3SA681KN3AX02F
C _{INJ}	1	Capacitor, ceramic, 4.7 nF, 300 VAC, Y2	MuRata	DE2E3SA472MA3BX02F
C _{D1}	1	Capacitor, ceramic, 4.7 nF, 50 V, 0603	Various	–
C _{D2}	1	Capacitor, ceramic, 22 nF, 50 V, 0603	Various	–
C _{D3}	1	Capacitor, ceramic, 4.7 nF, 50 V, 0603	Various	–
C _{G1}	1	Capacitor, ceramic, 10 nF, 50 V, 0603	Various	–
C _{G2}	1	Capacitor, ceramic, 10 pF, 50 V, 0603	Various	–
C _{VDD}	1	Capacitor, ceramic, 1 μF, 25 V, X7R, 0603	Various	–
D _{INJ}	1	TVS diode, bidirectional, 24 V, SOD-323	Eaton	STS321240B301
R _{D1}	1	Resistor, 1 kΩ, 0.1 W, 0603	Various	–
R _{D1A}	1	Resistor, 50 Ω, 0.1 W, 0603	Various	–
R _{D2}	1	Resistor, 200 Ω, 0.1 W, 0603	Various	–
R _{D3}	1	Resistor, 698 Ω, 0.1 W, 0603	Various	–
R _G	1	Resistor, 1.5 kΩ, 0.1 W, 0603	Various	–
U ₁	1	TPSF12C1-Q1 common-mode AEF IC for single-phase power systems	Texas Instruments	TPSF12C1QDYRQ1

(1) See the [Third-Party Products Disclaimer](#).

More generally, the TPSF12C1-Q1 AEF IC is designed to operate with a wide range of passive filter components and system parameters.

9.2.1.2.1 Sense Capacitors

The sense pins of the TPSF12C1-Q1 feed into a second-order high-pass filter and signal combiner within the IC, which rejects the line-frequency and DM components of the power line voltages, extracting the high-frequency CM component. These sense pins operate in pairs: SENSE1A and SENSE2A connect to SENSE1B and SENSE2B, respectively.

The sense pins externally interface to the power lines using two Y-rated capacitors, designated as C_{SEN1} and C_{SEN2} in Figure 9-2. Choose Y2-rated sense capacitors of 680 pF, 300 VAC in this application to establish voltages at the SENSE pins of 3-V peak-to-peak when operating at maximum line voltage.

9.2.1.2.2 Inject Capacitor

The INJ node interfaces to a power line using a Y-rated capacitor, designated as C_{INJ} in Figure 9-2. Choose a Y2-rated inject capacitor of 4.7 nF, 300 VAC in this design to accommodate an AC swing with at least a 2-V margin of headroom from the positive and negative supply rails.

The INJ pin biases at half the VDD supply voltage. Assuming a 12-V supply rail and allowing 2 V of upper and lower headroom, this implies that a swing of ±4 V is available around the DC operating point.

9.2.1.2.3 Compensation Network

The CM noise signal derived from the internal sensing filter and summation network of the TPSF12C1-Q1 is internally inverted and amplified by a gain stage. The components between the COMP1 and COMP2 pins of the IC, designated as R_G, C_{G1} and C_{G2} in Figure 9-2, set the gain characteristic.

More specifically, resistor R_G establishes a high midband AEF gain at frequencies where EMI filtering is required. Capacitor C_{G1} increases the impedance of that branch at low frequencies, which sets a lower AEF amplifier gain

So while an injection network is needed for stability, it also adds impedance in series with inject capacitor, thus compromising EMI mitigation. As shown below, the user can minimize the impact on performance with careful and appropriate design.

Illustrated in Figure 9-4, at low frequencies in the range of 5 kHz to 50 kHz, components R_{D1} and C_{D2} provide compensation and R_{D3} damps the effects of LC resonance. At higher frequencies (above 10 kHz), the dominant component impedance of each branch transitions to enable better attenuation performance:

- R_{D1} transitions to C_{D1}
- C_{D2} transitions to R_{D2}
- R_{D3} transitions to C_{D3}

Finally, C_{D1} transitions to R_{D1A} if needed for phase margin of the AEF loop at high frequencies, typically above 100 kHz.

When viewed in a clockwise direction, Figure 9-4 shows these transitions in sequence as frequency increases.

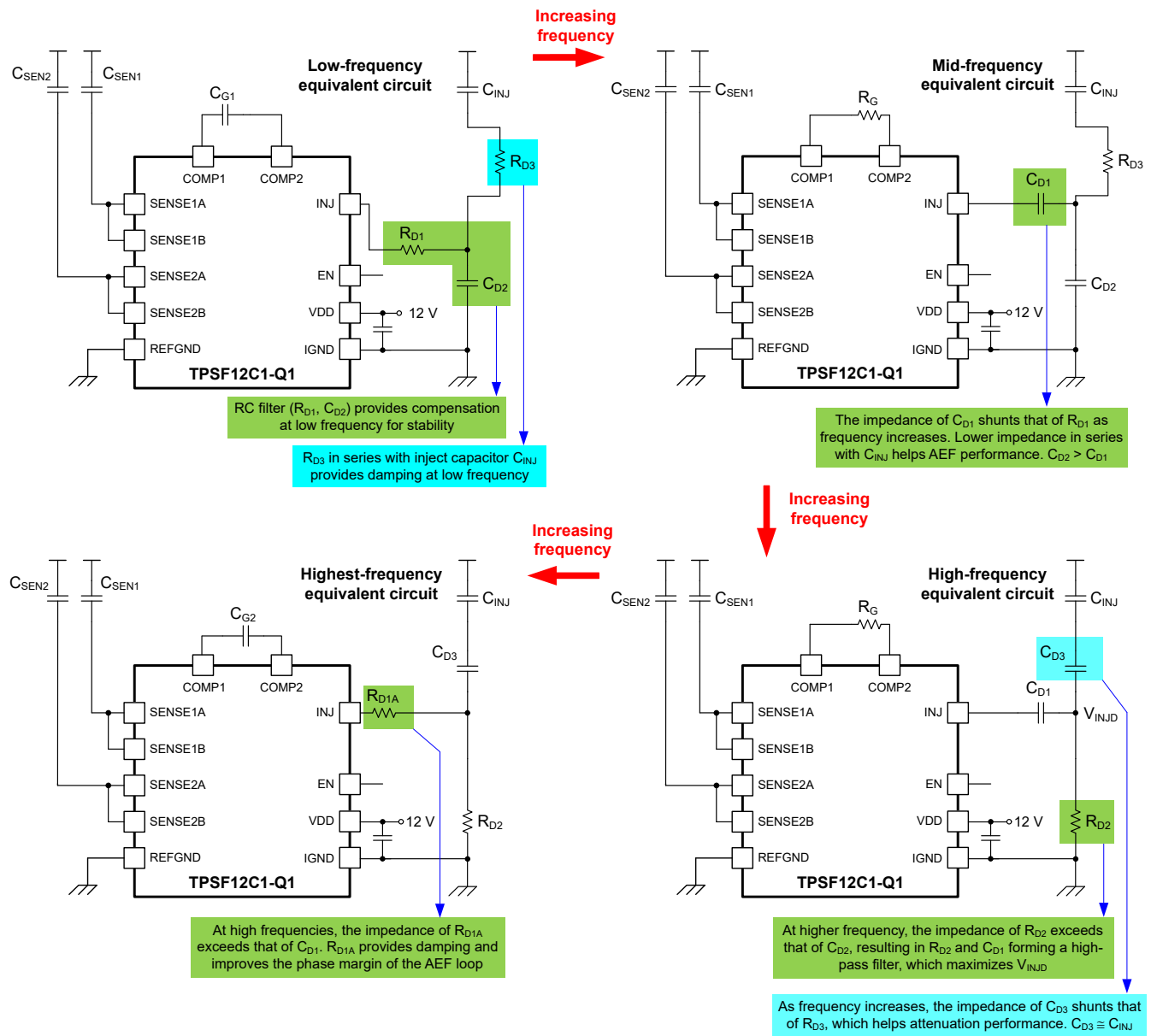


Figure 9-4. Dominant Components of the Injection Network vs Frequency

Below are basic guidelines to select the component values for the injection network:

1. The undamped loop gain characteristic is likely to be unstable within the range of 5 kHz to 50 kHz, which, as mentioned previously, relates to an LC resonance between CM choke inductance and inject capacitance. Observe from circuit simulation – or by using the TPSF12C1-Q1 [quickstart calculator](#) – the frequency, $f_{LFstability}$, at which the phase crosses -180° with positive gain, indicating negative gain margin.
2. Choose a corner frequency with R_{D1} and C_{D2} equal to one fifth of the instability frequency:

$$\frac{1}{2\pi \cdot R_{D1} \cdot C_{D2}} = \frac{f_{LFstability}}{5} \quad (2)$$

Assigning $R_{D1} = 1 \text{ k}\Omega$ and assuming instability at 35 kHz, use [Equation 3](#) to find a value for the capacitance of C_{D2} :

$$C_{D2} [\text{nF}] = \frac{5000}{2\pi \cdot R_{D1} [\text{k}\Omega] \cdot f_{LFstability} [\text{kHz}]} = \frac{5000}{2\pi \cdot 1 \cdot 35} = 22 \text{ nF} \quad (3)$$

3. Select $C_{D1} < C_{D2}$, where a typical choice is $C_{D1} = C_{D2}/5 = 4.7 \text{ nF}$.
4. Choose the resistance of R_{D2} such that the R_{D2}, C_{D2} corner frequency is equal to that of R_{D1}, C_{D1} :

$$R_{D2} [\Omega] = \frac{R_{D1} [\Omega] \cdot C_{D1} [\text{nF}]}{C_{D2} [\text{nF}]} = \frac{R_{D1} [\Omega]}{5} = \frac{1000}{5} = 200 \Omega \quad (4)$$

5. Select the resistance of R_{D3} to damp the resonance around the instability frequency, $f_{LFstability}$.
 - A typical choice for R_{D3} is 500 Ω to 1 k Ω .
 - Assign C_{D3} equal to C_{INJ} or a suitable value such that the R_{D3}, C_{D3} corner frequency is less than switching frequency.
 - A lower resistance for R_{D3} results in more damping but at the penalty of reduced high-frequency attenuation (or forces a higher value for C_{D3} to maintain the applicable corner frequency below the switching frequency).
6. Select a resistance for R_{D1A} of 50 Ω to improve the phase margin of the AEF loop (if needed).

9.2.1.2.5 Surge Protection

While the sense pins have internal clamp protection, the higher value of inject capacitance produces larger currents during surge events and thus requires external protection. Place a bidirectional TVS diode on the low-voltage side of the inject capacitor with standoff voltage of 24 V. Using the SOD-323 packaged device given in [Table 9-2](#), clamping occurs at 40 V and 50 V with surge currents of 1 A and 8 A, respectively.

9.2.1.3 Application Curves

Unless otherwise indicated, $V_{VDD} = V_{EN} = 12 \text{ V}$.

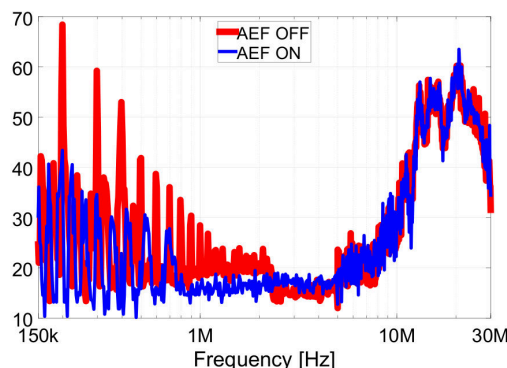
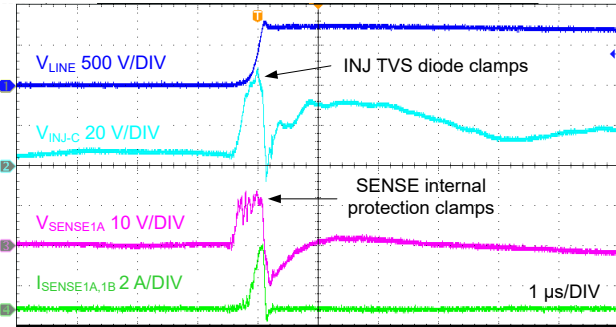
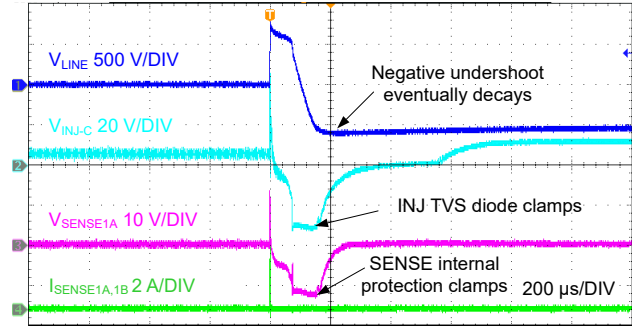


Figure 9-5. EMI Mitigation Result with AEF On and Off (EN Tied High and Low)

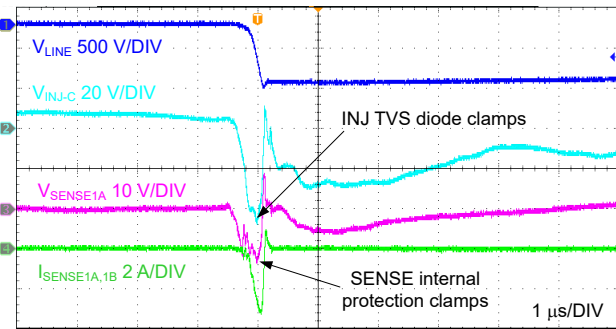


(a)

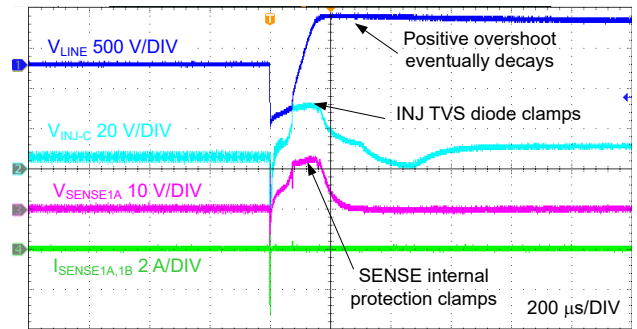


(b)

Figure 9-6. IEC 61000-4-5 Positive Surge, 5-kV Single Strike – 1 μ s/div (a), 200 μ s/div (b)

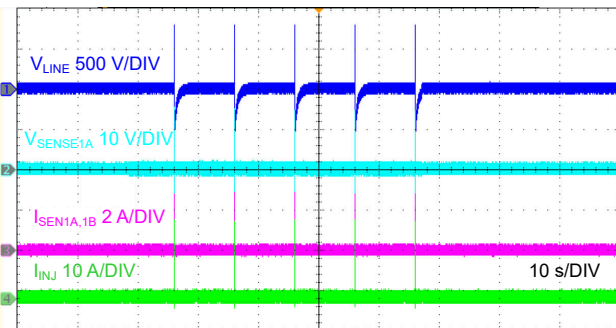


(a)

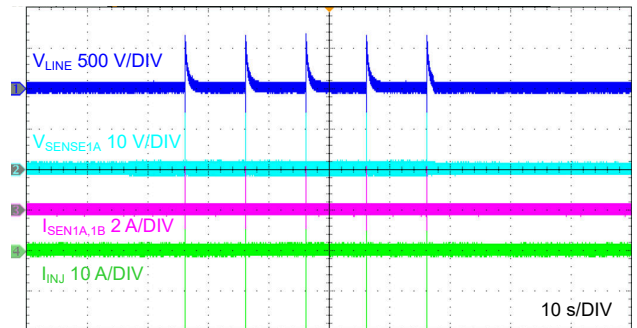


(b)

Figure 9-7. IEC 61000-4-5 Negative Surge, 5-kV Single Strike – 1 μ s/div (a), 200 μ s/div (b)



(a)



(b)

Figure 9-8. IEC 61000-4-5 Surge, 5-kV Repetitive Strike at 10-Second Intervals – Positive (a), Negative (b)

9.3 Power Supply Recommendations

The TPSF12C1-Q1 AEF IC operates over a wide supply voltage range of 8 V to 16 V (typically 12 V) and is referenced to chassis ground of the system. The characteristics of this VDD bias supply must be compatible with the *Absolute Maximum Ratings* and *Recommended Operating Conditions* in this data sheet. In addition, the VDD supply must be capable of delivering the required supply current to the loaded AEF circuit.

The supply rail can already be present in the system or can be derived using a low-cost solution with an auxiliary winding from an isolated flyback regulator. Connect a 1- μ F ceramic capacitor close to the VDD and IGND pins of the TPSF12C1-Q1. Ensure that the VDD ripple voltage is less than 50 mV peak-to-peak.

9.4 Layout

Proper PCB design and layout is important in active EMI circuits (where high regulator voltage and current slew rates exist) to achieve reliable device operation and design robustness. Furthermore, the EMI performance of the design depends to a large extent on PCB layout.

9.4.1 Layout Guidelines

The following list summarizes the essential guidelines for PCB layout and component placement to optimize AEF performance. [Figure 9-9](#) and [Figure 9-10](#) show a recommended layout for the TPSF12C1-Q1 with optimized placement and routing of the IC and small-signal components. [Figure 9-11](#) shows an example filter board design with CM chokes, X-capacitors and Y-capacitors along with a receptacle for easy connection of an AEF daughterboard.

- *Route the sense lines S1 and S2 away from the INJ line.* Avoid coupling between sense and inject traces.
- *Place a ceramic capacitor close to the VDD and IGND pins.* Minimize the area of the loop to the VDD and IGND pins.
- *Place the compensation network components close to the COMP1 and COMP2 pins.* Reduce noise sensitivity of the feedback compensation network path by placing the R_G - C_{G1} - C_{G2} network close to the COMP pins. COMP2 is the inverting input to the AEF amplifier and represents a high-impedance node sensitive to noise.
- *Provide enough PCB area for proper heatsinking.* Use sufficient copper area to achieve a low thermal impedance. Provide adequate heatsinking for the TPSF12C1-Q1 to keep the junction temperature below 150°C. A top-side ground plane is an important heat-dissipating area. Use several heat-sinking vias to connect IGND (pin 14) and REFGND (pin 9) to the PCB ground plane.

9.4.2 Layout Example

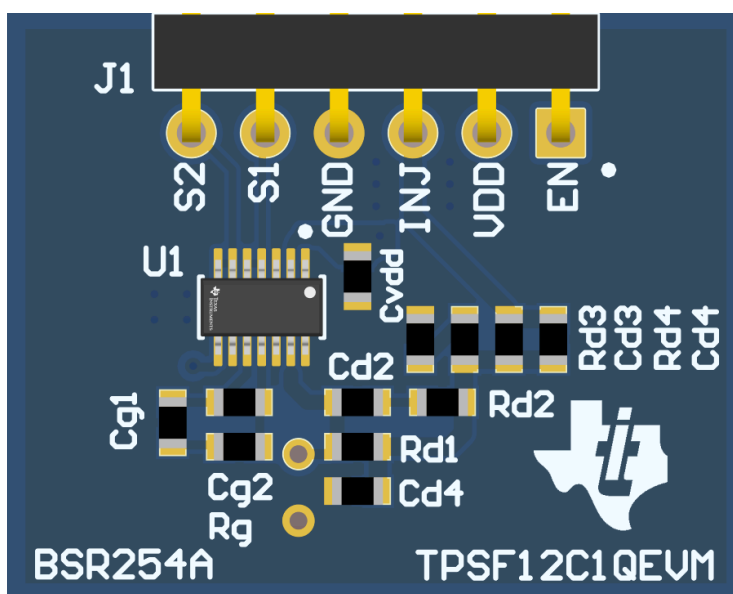


Figure 9-9. Typical Layout

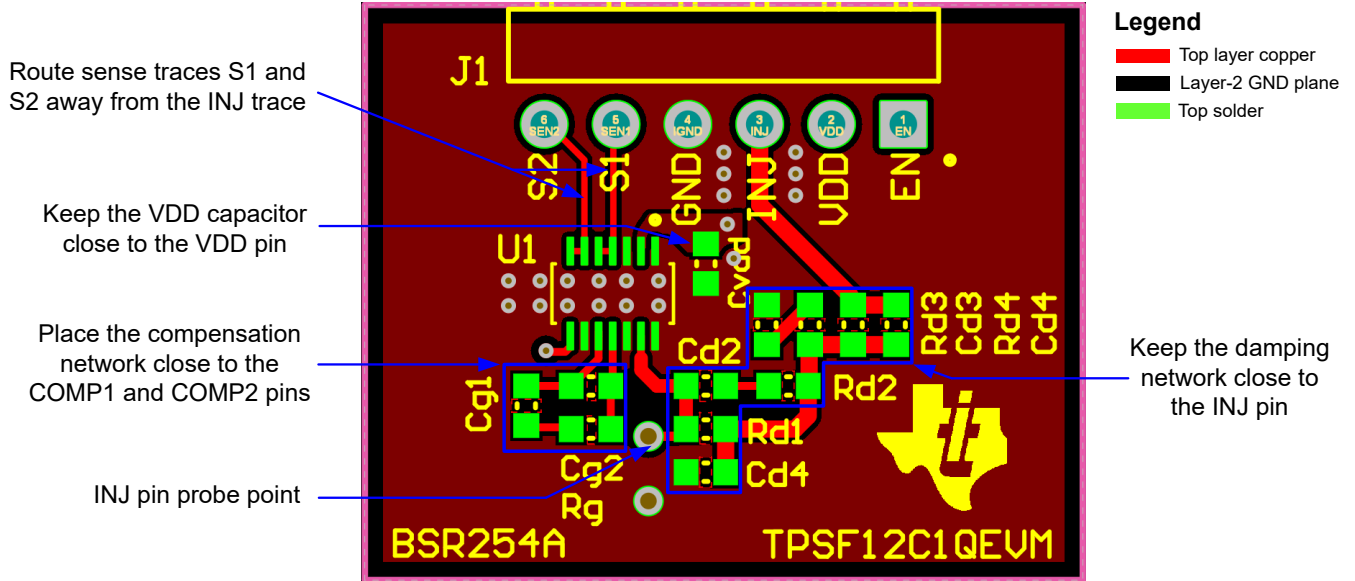


Figure 9-10. Typical Top-Layer Design

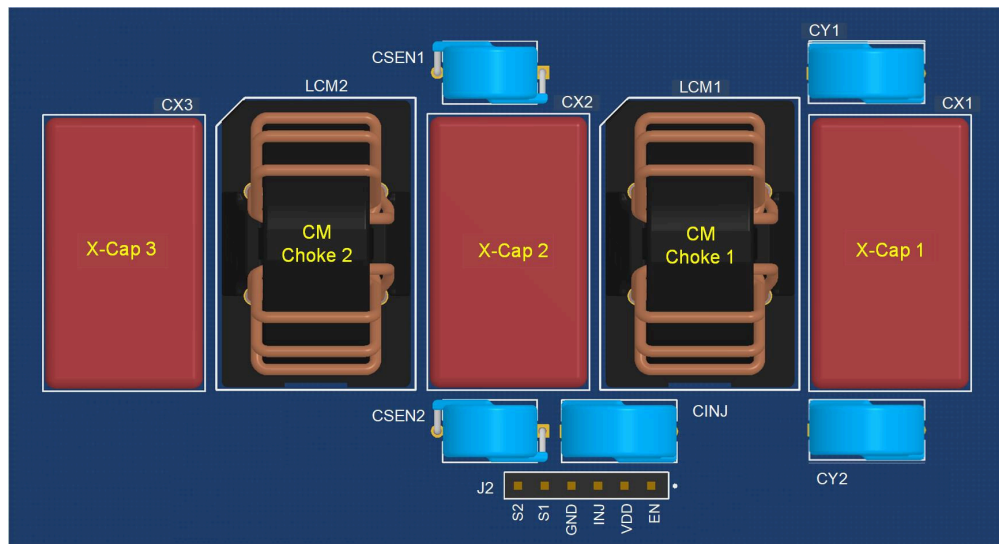


Figure 9-11. Typical Filter Board Design

ADVANCE INFORMATION

10 Device and Documentation Support

10.1 Device Support

10.1.1 Third-Party Products Disclaimer

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10.1.2 Development Support

All AEF devices from the family shown in [Table 10-1](#) are rated for an ambient temperature up to 105°C and are [functional safety capable](#).

Table 10-1. Common-mode AEF IC Family

DEVICE	ORDERABLE PART NUMBER	PHASES	GRADE	JUNCTION TEMPERATURE RANGE
TPSF12C1-Q1	TPSF12C1QDYRQ1	1	Automotive	-40°C to 150°C
TPSF12C3-Q1	TPSF12C3QDYRQ1	3	Automotive	-40°C to 150°C
TPSF12C1	TPSF12C1DYR	1	Commercial	-40°C to 150°C
TPSF12C3	TPSF12C3DYR	3	Commercial	-40°C to 150°C

For development support see the following:

- [TPSF12C1-Q1 Quickstart calculator](#)
- [TPSF12C1-Q1 EVM Altium layout source files](#)
- [TPSF12C1-Q1 PSICE for TI and SIMPLIS simulation models](#)
- For TI's reference design library, visit [TI Reference Design library](#)
- To design a low-EMI power supply, review TI's comprehensive [EMI Training Series](#)
- TI Reference Designs:
 - [Automotive wide \$V_{IN}\$ front-end reference design for digital cockpit processing units](#)
- Technical Articles:
 - Texas Instruments, [How to reduce EMI and shrink power-supply size with an integrated active EMI filter](#)
 - Texas Instruments, [How device-level features and package options can help minimize EMI In automotive designs](#)
 - Texas Instruments, [How to use slew rate for EMI control](#)
- White Papers:
 - Texas Instruments, [Valuing Wide \$V_{IN}\$, Low-EMI Synchronous Buck Circuits for Cost-Effective, Demanding Applications](#)
 - Texas Instruments, [An Overview of Conducted EMI Specifications for Power Supplies](#)
 - Texas Instruments, [An Overview of Radiated EMI Specifications for Power Supplies](#)
- To view a related device of this product, see the [TPSF12C3-Q1](#) three-phase active EMI filter for common-mode EMI mitigation

10.2 Documentation Support

10.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [An Engineer's Guide To EMI In DC/DC Regulators](#) e-book
- Texas Instruments, [Reduce Buck Converter EMI and Voltage Stress by Minimizing Inductive Parasitics](#) ADJ article
- Texas Instruments, [Designing High Performance, Low-EMI, Automotive Power Supplies](#) application report
- Texas Instruments, [EMI Filter Components And Their Nonidealities For Automotive DC/DC Regulators](#) technical brief

10.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.4 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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10.5 Trademarks

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10.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

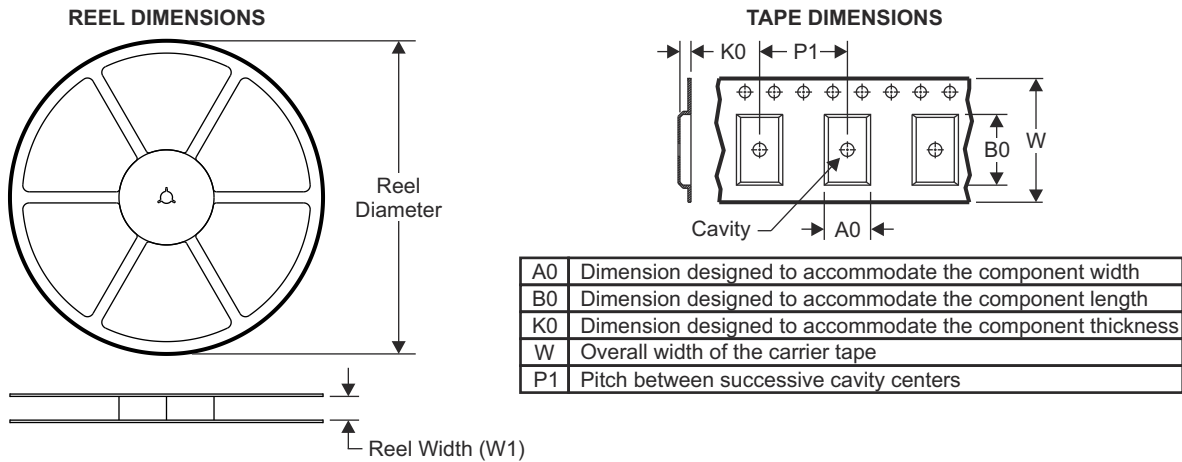
10.7 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

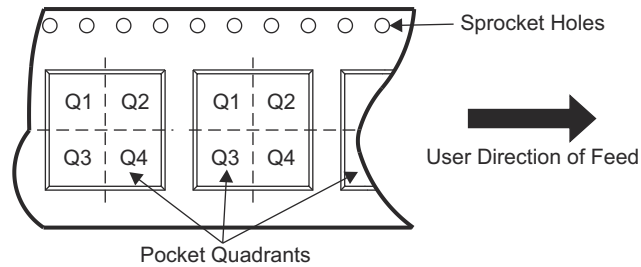
11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this datasheet, refer to the left-hand navigation.

11.1 Tape and Reel Information

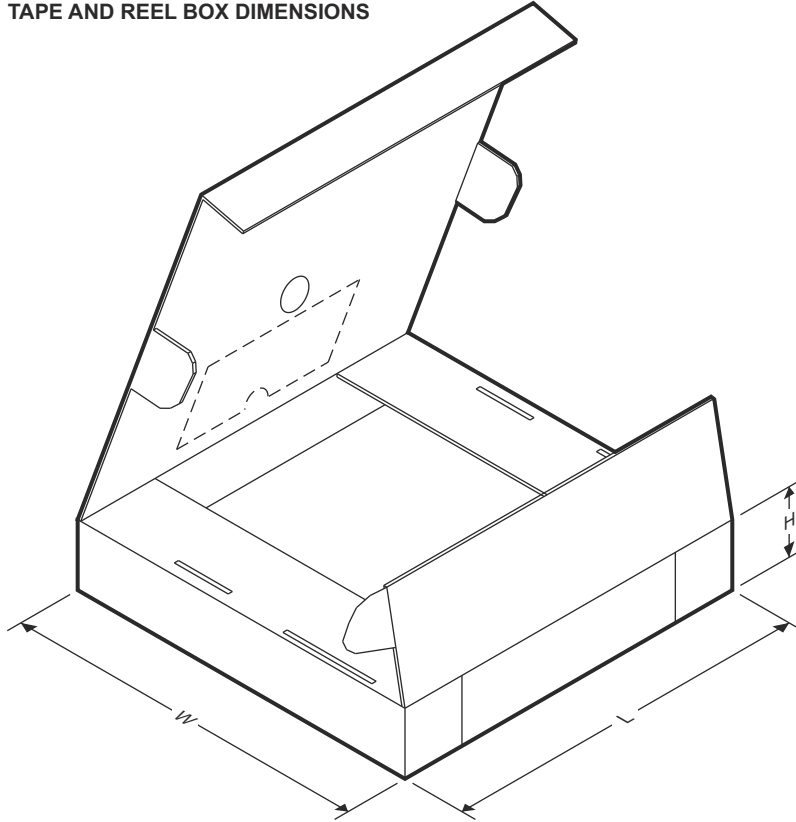


QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPSF12C1QDYRQ1	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3

TAPE AND REEL BOX DIMENSIONS



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPSF12C1QDYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8

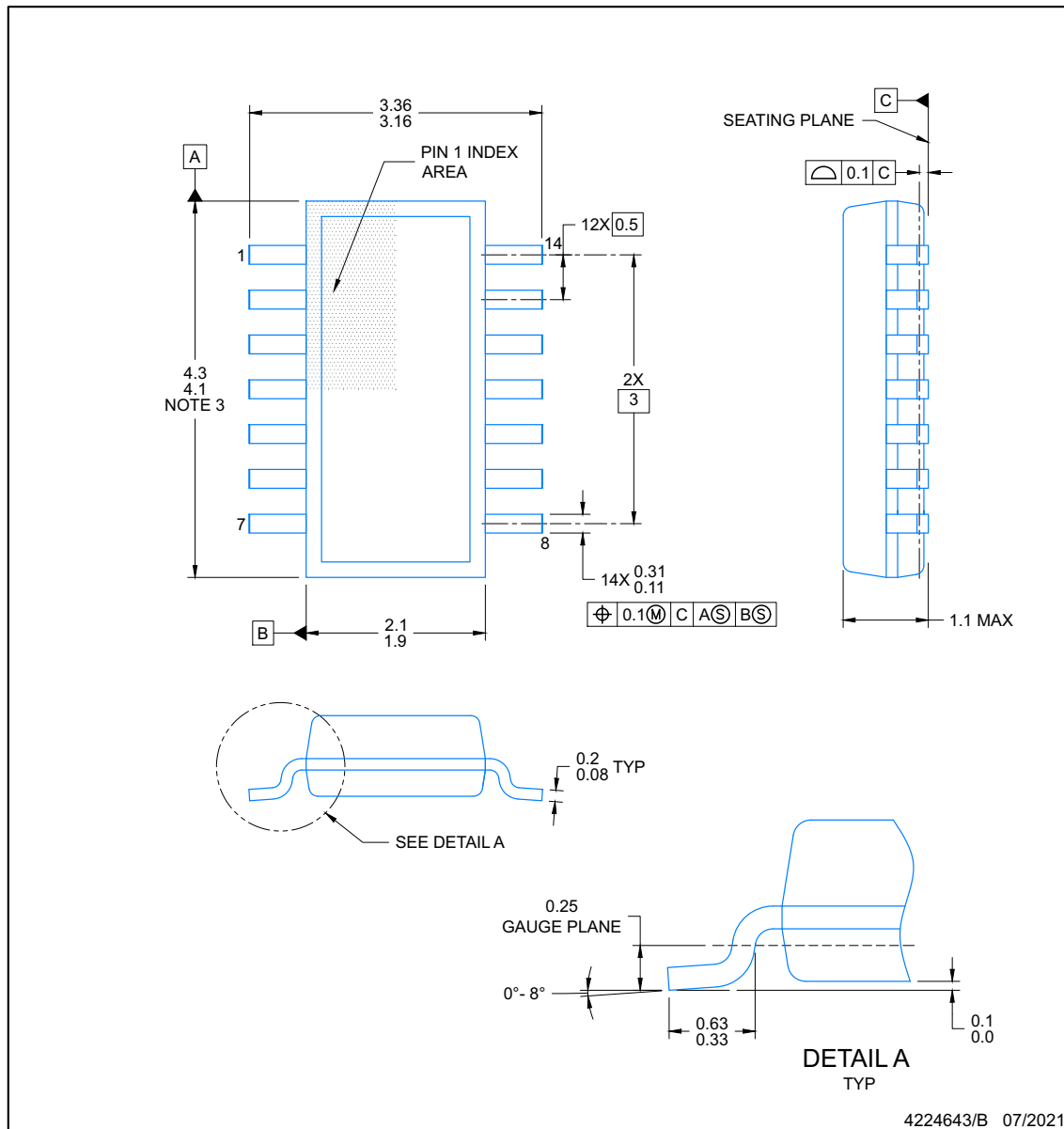
ADVANCE INFORMATION

PACKAGE OUTLINE

DYY0014A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



4224643/B 07/2021

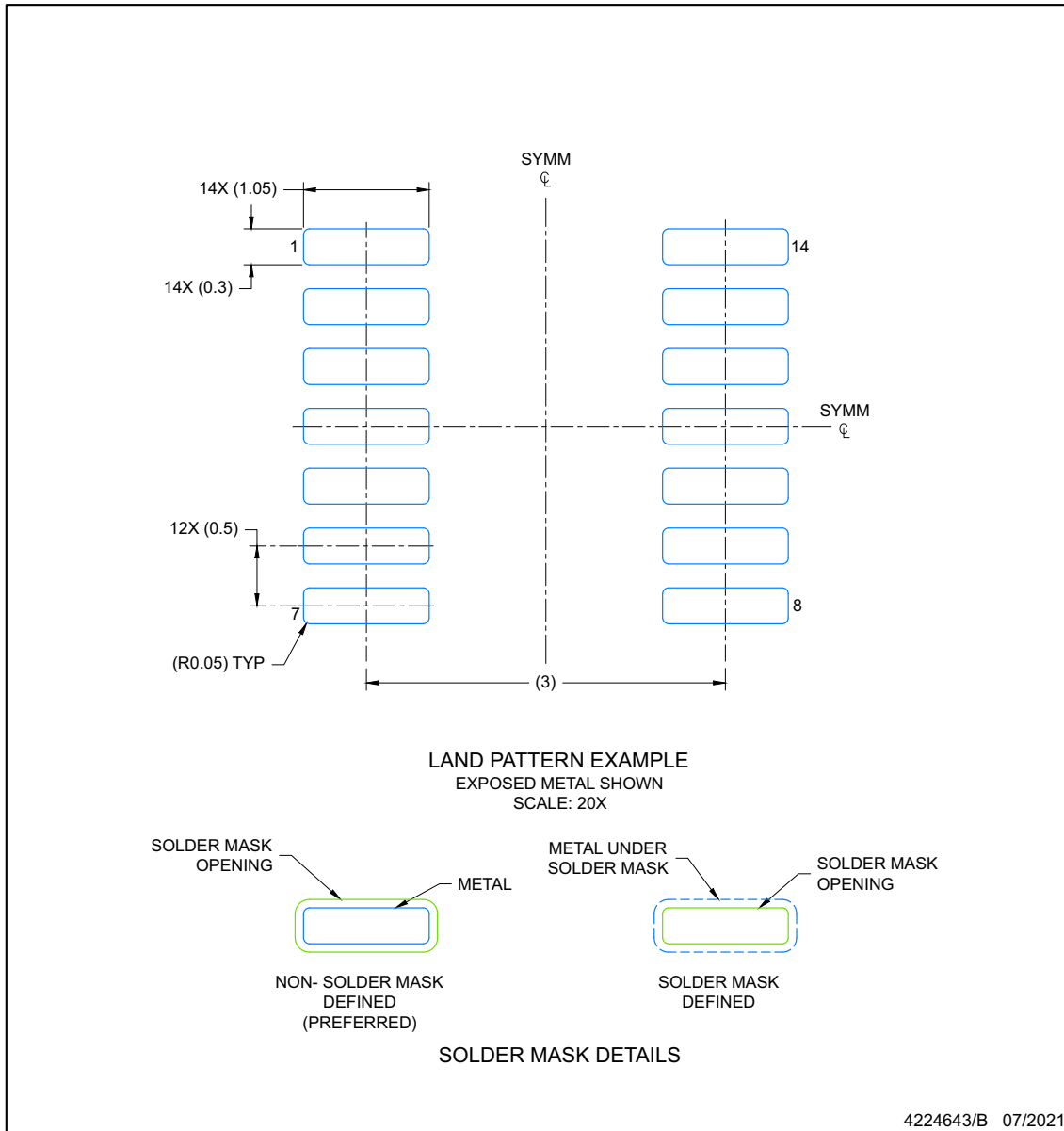
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB

DYY0014A

EXAMPLE BOARD LAYOUT
SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



ADVANCE INFORMATION

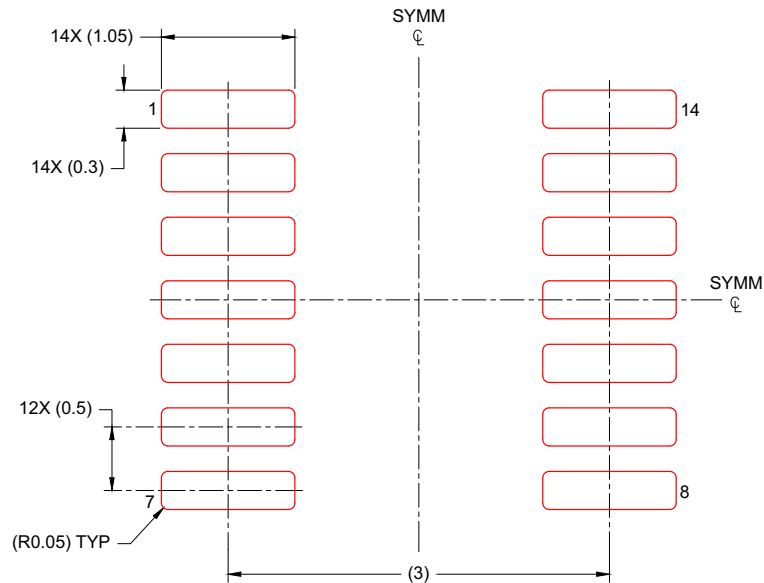
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN
SOT-23-THIN - 1.1 mm max height

DYY0014A

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

4224643/B 07/2021

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

ADVANCE INFORMATION

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
P12C1QDYRQ1	ACTIVE	SOT-23-THIN	DYY	14	3000	TBD	Call TI	Call TI	-40 to 150		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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